

Application No.: 10/643,944

AMENDMENT TO SPECIFICATION

Please amend the paragraph beginning at page 30 line 16 as follows:

--In the laser wafer of the present embodiment, the intermediate layer 31 is a GaN layer with a thickness of 60 nm, which is formed between an active layer 101 and a cap layer 22 and which has a stacked structure composed of an ~~undoped~~ undoped layer 31a with a thickness of 15 nm and a diffusion-blocking layer 31b with a thickness of 45 nm. The diffusion-blocking layer 31b has an Si impurity concentration of, for example, about $3 \times 10^{19} \text{ cm}^{-3}$, and adjoins the cap layer 22.--